(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
14 October 2004 (14.10.2004)

PCT

(10) International Publication Number
WO 2004/088767 A1

(51) International Patent Classification[7]: H01L 51/30, 51/10

(21) International Application Number: PCT/JP2004/004350

(22) International Filing Date: 26 March 2004 (26.03.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
2003-096208 · 31 March 2003 (31.03.2003) JP

(71) Applicant *(for all designated States except US)*: **CANON KABUSHIKI KAISHA** [JP/JP]; 3-30-2, Shimomaruko, Ohta-ku, Tokyo 1468501 (JP).

(72) Inventor; and

(75) Inventor/Applicant *(for US only)*: **KOGANEI, Akio,** [JP/JP]; c/o Canon Kabushiki Kaisha, 3-30-2, Shimomaruko, Ohta-ku, Tokyo 1468501 (JP).

(74) Agents: **OKABE, Masao** et al.; No. 602, Fuji Bldg., 2-3, Marunouchi 3-chome, Chiyoda-ku, Tokyo 1000005 (JP).

(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:
— *with international search report*

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: ORGANIC THIN FILM TRANSISTOR

(57) Abstract: An organic thin film transistor utilizing an organic semiconductor film is composed of a first substrate, a gate electrode, a gate insulation film, an organic semiconductor film, a source electrode, a drain electrode, a protective film and a second substrate, and produced by forming a gate electrode, a gate insulation film, an organic semiconductor film, a source electrode, and a drain electrode on a first substrate, forming a protective film on a second substrate, and superposing a surface, bearing the organic semiconductor film, of the first substrate upon a surface, bearing the protective film, of the second substrate.

WO 2004/088767 A1